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FAIRCHILD

SEMICONDUCTOR®

November 2013

FQB55N10 N-Channel QFET® MOSFET

100 V, 55 A, 26 mΩ

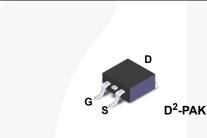
Description

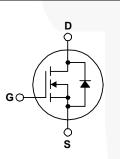
This N-Channel enhancement mode power MOSFET is • 55 A, 100 V, $R_{DS(on)}$ = 26 m Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state D = 27.5 A Low Gate Charge (Typ. 75 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 130 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- I_D = 27.5 A

- 175°C Maximum Junction Temperature Rating





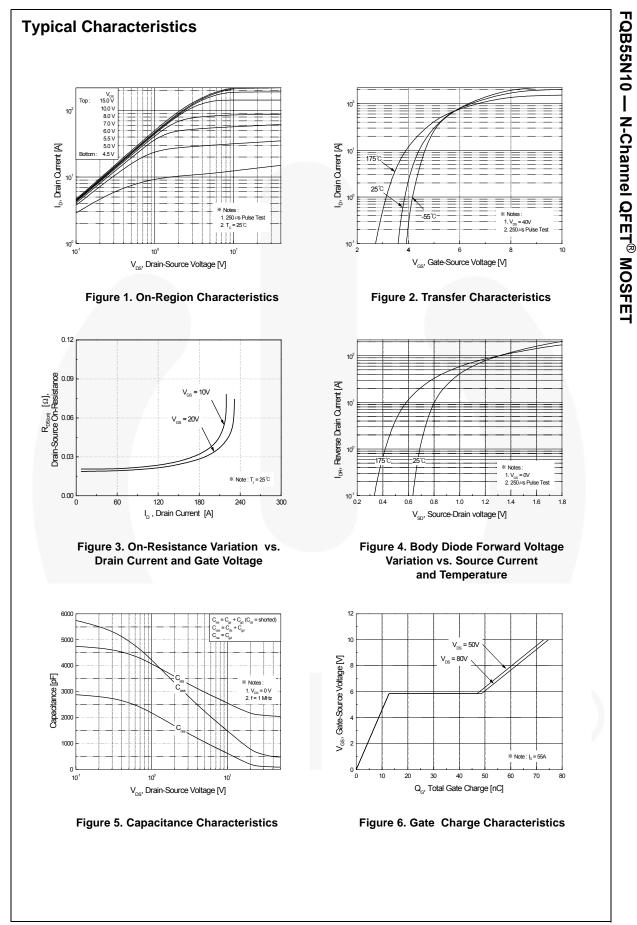
Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

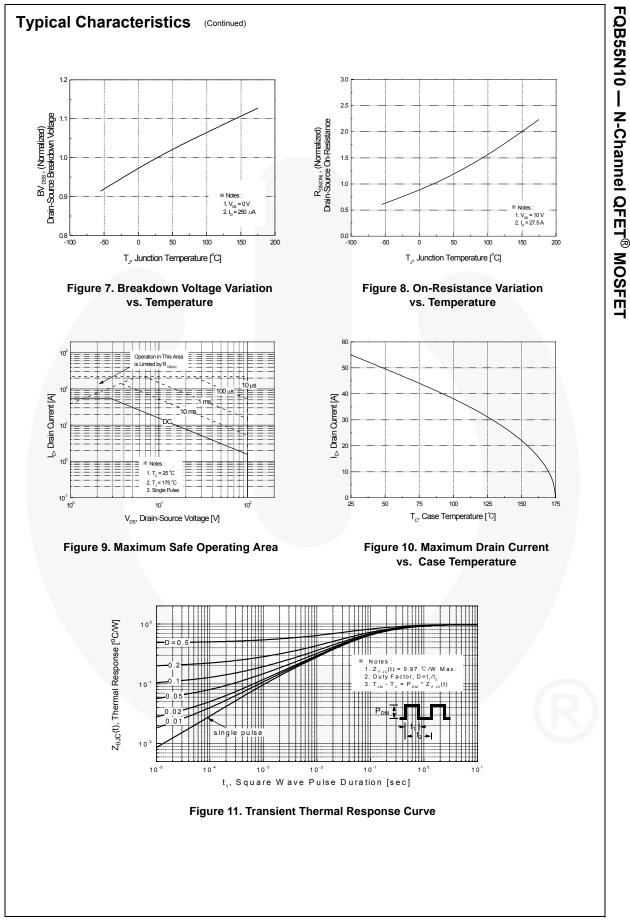
Symbol	Parameter	FQB55N10TM	Unit	
V _{DSS}	Drain-Source Voltage	100	V	
ID	Drain Current - Continuous ($T_C = 25^{\circ}C$)	55	A	
	- Continuous (T _C = 100°C)	38.9	A	
I _{DM}	Drain Current - Pulsed (Note 1)	220	A	
V _{GSS}	Gate-Source Voltage	± 25	V	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)	1100	mJ	
I _{AR}	Avalanche Current (Note 1)	55	A	
E _{AR}	Repetitive Avalanche Energy (Note 1)	15.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.0	V/ns	
P _D	Power Dissipation $(T_A = 25^{\circ}C)^{*}$	3.75	W	
	Power Dissipation ($T_C = 25^{\circ}C$)	155	W	
	- Derate above 25°C	1.03	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +175	°C	
TL	Maximum lead temperature for soldering,1/8" from case for 5 seconds	300	°C	

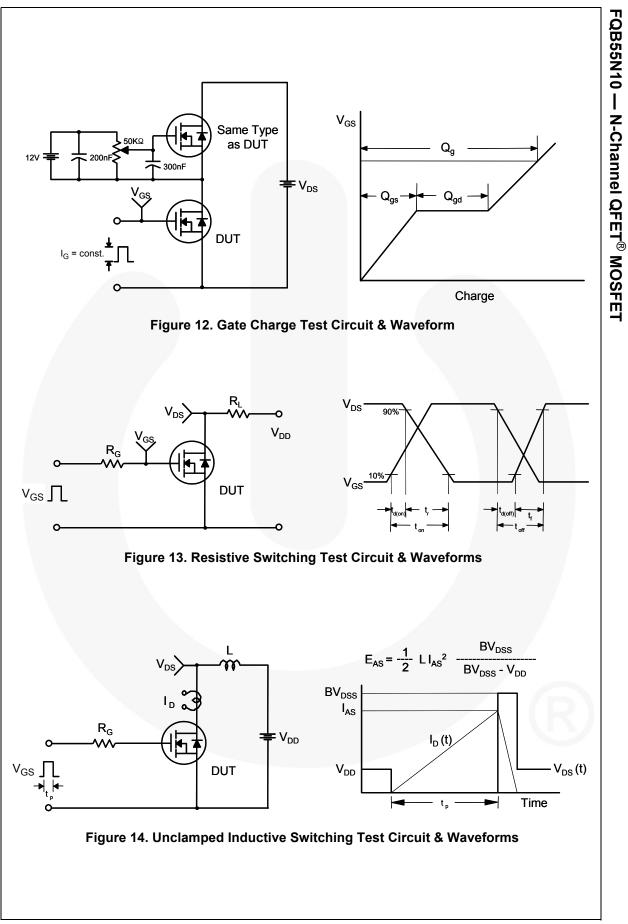
Thermal Characteristics

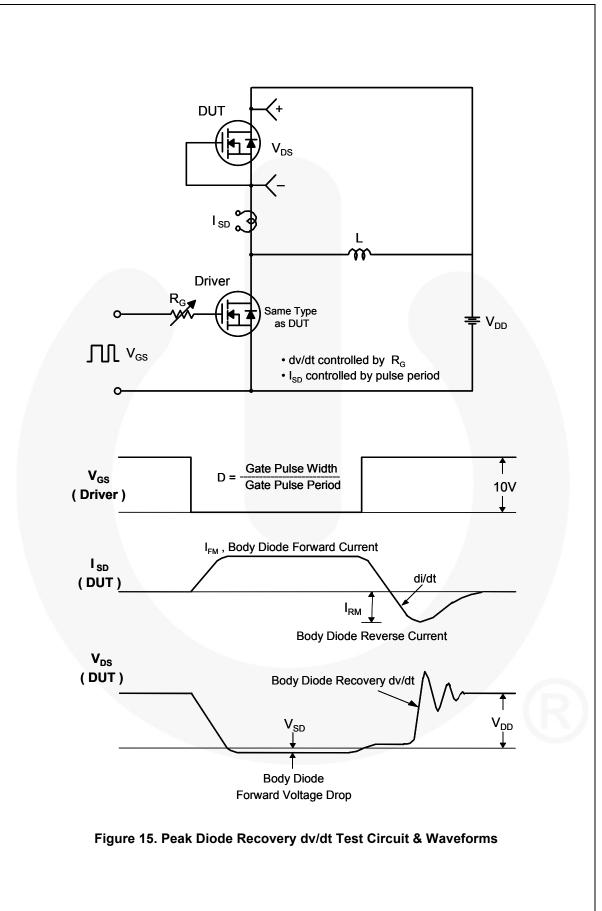
Symbol	Parameter	FQB55N10TM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.97	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	40	

Part Number Top Mark Pa		Pac	kage Packing Method Reel		Size	Tape Width		Quantity			
FQB5	FQB55N10TM FQB55N10 D ² -		PAK Tape and Reel 330			330	mm	24 mm		800 units	
Electri	cal Cha	racteristics	T _C = 25°	C unless otl	nerwise noted.						
Symbol		Parameter			Test Conditions			Min.	Тур. Ма		x. Unit
Off Cha	racterist	ics									
BV _{DSS}	Drain-Source Breakdown Voltage			V_{GS} = 0 V, I _D = 250 µA				100			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient			$I_D = 250 \mu\text{A}$, Referenced to 25°C					0.1		V/°C
I _{DSS}	Zero Gate	Zero Gate Voltage Drain Current		V _{DS} = 100 V, V _{GS} = 0 V					1	μA	
				V _{DS} = 80 V, T _C = 150°C					10	μA	
I _{GSSF}		y Leakage Current, F		V_{GS} = 25 V, V_{DS} = 0 V						100	nA
I _{GSSR}	Gate-Bod	y Leakage Current, R	everse	V _{GS} =	-25 V, V _{DS} =	0 V				-100	nA
On Cha	racterist	ics									
V _{GS(th)}	Gate Thre	Sate Threshold Voltage		V _{DS} =	V _{GS} , I _D = 25	0 μΑ		2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS} = 10 V, I _D = 27.5 A					0.021	0.026	Ω	
9 _{FS}	Forward Transconductance		V _{DS} = 40 V, I _D = 27.5 A				38		S		
Dynami	ic Charad	cteristics									
C _{iss}	Input Cap	acitance		V _{DS} =	25 V, V _{GS} = 0 V, MHz	0 V,			2100	2730	pF
C _{oss}	Output Ca	apacitance		f = 1.0					640	830	pF
C _{rss}	Reverse 1	Fransfer Capacitance							130	170	pF
Switchi	ng Chara	acteristics									
t _{d(on)}	Turn-On Delay Time			V _{DD} = 50 V, I _D = 55 A,				25	60	ns	
t _r	Turn-On F	Rise Time		$R_G = 2$	-				250	510	ns
t _{d(off)}	Turn-Off D	Delay Time			0 11				110	230	ns
t _f	Turn-Off F	all Time					Note 4)		140	290	ns
Qg	Total Gate	e Charge		V _{DS} =	80 V, I _D = 55	iА,			75	98	nC
Q _{gs}	Gate-Sou	rce Charge		V _{GS} =		-			13		nC
Q _{gd}	Gate-Drai	n Charge		(Note 4					36		nC
Drain-S	ource Di	ode Characteris	tics a	nd Max	imum Ra	tings					
I _S	Maximum Continuous Drain-Source Diode Forward Current							55	A		
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current							220	Α		
V _{SD}	Drain-Sou	rce Diode Forward V	oltage	V _{GS} = 0 V, I _S = 55 A					1.5	V	
t _{rr}	Reverse F	Recovery Time		V _{GS} = 0 V, I _S = 55 A,				100		ns	
Q _{rr}	Reverse F	Recovery Charge		dl _F / dt = 100 A/μs					380		nC









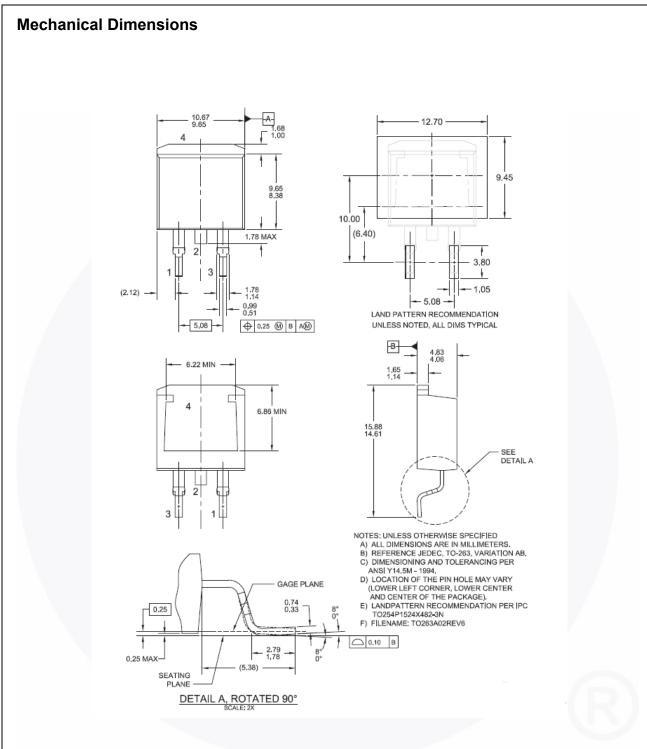


Figure 16. TO263 (D²PAK), Molded, 2-Lead, Surface Mount

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http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT263-002

FQB55N10 — N-Channel QFET[®] MOSFET



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	•	Rev. I66

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